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TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type (Four Darlington Power Transistors in One)

MP4104

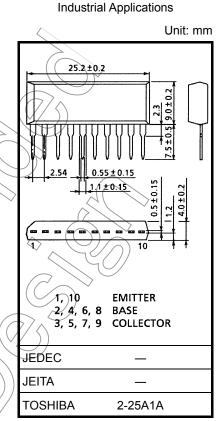
High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

- Small package by full molding (SIP 10 pins)
- High collector power dissipation (4-device operation)
 P_T = 4 W (Ta = 25°C)
- High collector current: IC (DC) = 4 A (max)
- High DC current gain: $h_{FE} = 2000 \text{ (min)} (V_{CE} = 2 \text{ V}, I_C = 1.5 \text{ A})$

Absolute Maximum Ratings (Ta = 25°C)

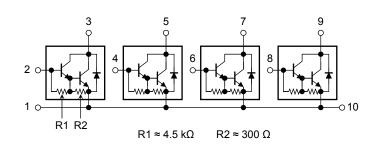
Characteristics		Symbol	Rating	Unit
Collector-base voltage		V _{CBO}	120	> v
Collector-emitter voltage		V _{CEO}	100	V
Emitter-base voltage		V _{EBO}	6	V
Collector current	DC	Ic <	4	
	Pulse	ICP	6	A
Continuous base current		IB) 0.5	A
Collector power dissipation		(Pc	2.0	w
(1-device operation)		(FC)	2.0	
Collector power dissipation			4.0	w
(4-device operation)			4.0	\checkmark
Junction temperature		Tj <	(150/))	°C
Storage temperature ran	ge	T _{stg}	-55 to 150	°C



Weight: 2.1 g (typ.)

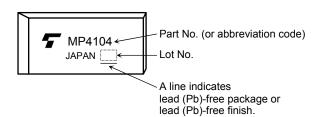
- Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
 - Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Array Configuration



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Marking



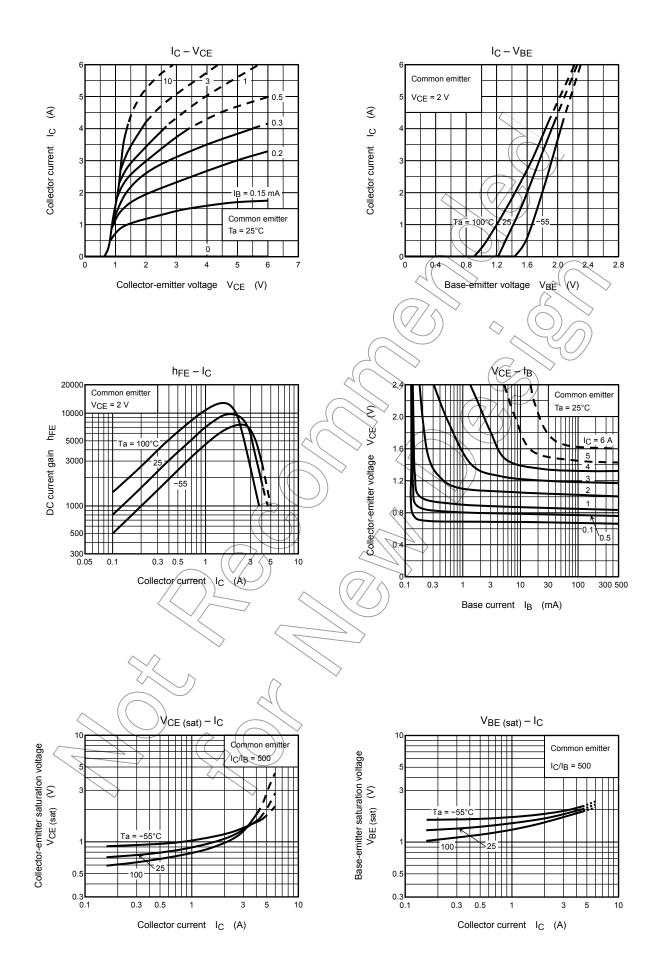
Thermal Characteristics

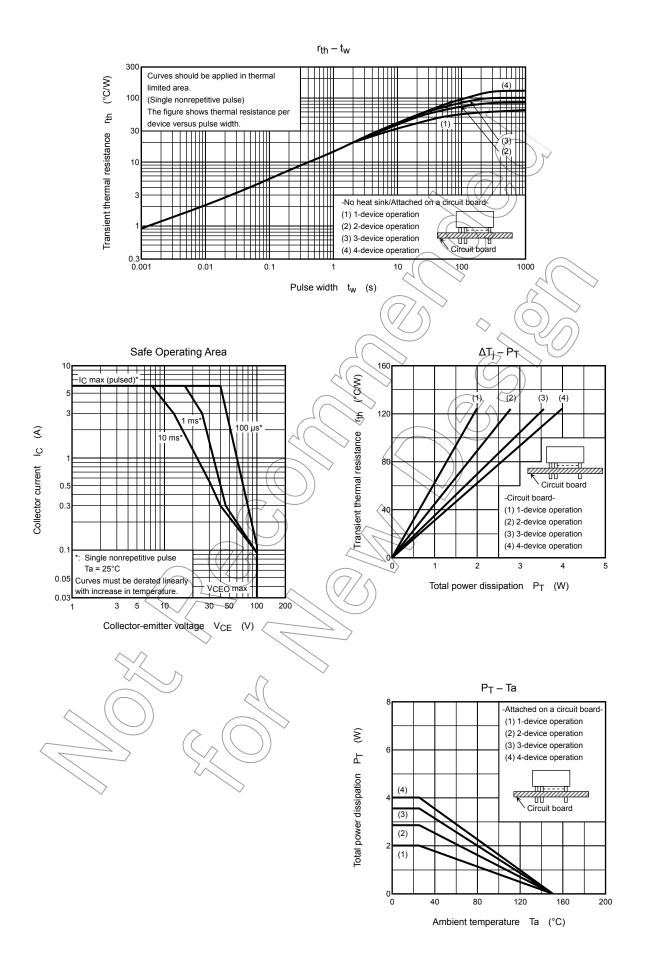
Characteristics	Symbol	Max	Unit	
Thermal resistance from junction to ambient $(4 \text{ device exerction}, Ta = 25^{\circ}\text{C})$	ΣR _{th (j-a)}	31.3	°C/W	
(4-device operation, Ta = 25°C) Maximum lead temperature for				
soldering purposes (3.2 mm from case for 10 s)	ΤL	260)) O°	

Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I _{CBO (}	V _{CB} = 120 V, I _E = 0 A	/ _	_	10	μA	
Collector cut-off current		ICEO	$V_{CE} = 100 \text{ V}, \text{ I}_{B} = 0 \text{ A}$			10	μA	
Emitter cut-off current		IEBQ	V _{EB} = 6 V, I _C = 0 A	0.5	_	2.5	mA	
Collector-base brea	akdown voltage	V (BR) CBO	$1_{C} = 1 \text{ mA}, I_{E} = 0 \text{ A}$	120	_	_	V	
Collector-emitter br	reakdown voltage	V (BR) CEO	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0 A	100		_	V	
DC current gain		hre (1)	$V_{CE} = 2 V, I_C = 7.5 A$	2000		15000		
		h _{FE} (2)	$V_{CE} = 2 V, t_{C} = 3.0 A$	1000	_	_	_	
Saturation voltage	Collector-emitter	VCE (sat)	I _C = 1.5 A, J _B ⇒ 3 mA	_	_	1.5	v	
	Base-emitter	⊃V _{BE (sat)} <	$I_{C} = 1.5 \text{ A}, I_{B} = 3 \text{ mA}$	_	_	2.0		
Transition frequence	y	ft	$V_{CE} = 2V, I_{C} = 0.5 A$	_	60	_	MHz	
Collector output ca	pacitance	C _{ob}	V _{CB} = 10 V, I _E = 0 A, f = 1 MHz	_	30	_	pF	
Switching time Fall time	ton	$\begin{array}{c} \text{Output} \\ \text{Input} \\ \text{Output} \\ $	_	0.3	_	μs		
	tstg			2.0	_			
	Fall time	t _f	$I_{B1} = -I_{B2} = 3 \text{ mA}$	—	0.4	_		

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